PCN Number:	20180606000	PCN Date:	June 08, 2018
Title:	Datasheet for THS6212		
Customer Contact:	PCN Manager	Dept:	Quality Services

Change Type:

☐	Assembly Site	☐	Design	☐	Wafer Bump Site
☐	Assembly Process	☒	Data Sheet	☐	Wafer Bump Material
☐	Assembly Materials	☐	Part number change	☐	Wafer Bump Process
☐	Mechanical Specification	☐	Test Site	☐	Wafer Fab Site
☐	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Materials
				☐	Wafer Fab Process

Notification Details

Description of Change:

Texas Instruments Incorporated is announcing an information only notification.
The product datasheet(s) is being updated as summarized below.
The following change history provides further details.

TEXAS INSTRUMENTS

THS6212

SBOS758B – MAY 2016 – REVISED MAY 2018

Changes from Revision A (March 2017) to Revision B **Page**

- Changed full-bias mode value from 21 mA to 23 mA in *Features* list 1
- Changed mid-bias mode value from 16.2 mA to 17.7 mA in *Features* list 1
- Changed low-bias mode value from 11.2 mA to 12.2 mA in *Features* list 1
- Added "With Exposed Thermal Pad" to pinout drawing description to *Pin Configuration and Functions* section 4
- Deleted I_{S+} quiescent current "T_A = –40°C to +85°C" test conditions and values from *Electrical Characteristics: V_S = ±12 V* table 7
- Deleted minimum and maximum full bias I_{S+} quiescent current values from*Electrical Characteristics: V_S = ±12 V* table 7
- Changed typical full bias I_{S+} quiescent current value from 21 mA to 23 mA in *Electrical Characteristics: V_S = ±12 V* table. 7
- Deleted minimum and maximum mid bias I_{S+} quiescent current values from *Electrical Characteristics: V_S = ±12 V* table... 7
- Changed typical mid bias I_{S+} quiescent current value from 16.2 mA to 17.7 mA in *Electrical Characteristics: V_S = ±12 V* table 7
- Deleted minimum and maximum low bias I_{S+} quiescent current values from *Electrical Characteristics: V_S = ±12 V* table ... 7
- Changed typical low bias I_{S+} quiescent current value from 11.2 mA to 12.2 mA in *Electrical Characteristics: V_S = ±12 V* table..... 7
- Deleted $I_{S–}$ quiescent current "T_A = –40°C to +85°C" test conditions and values from *Electrical Characteristics: V_S = ±12 V* table 7
- Deleted minimum and maximum full bias $I_{S–}$ quiescent current values 7
- Changed typical full bias $I_{S–}$ quiescent current value from 20 mA to 22 mA 7
- Deleted minimum and maximum mid bias $I_{S–}$ quiescent current values from *Electrical Characteristics: V_S = ±12 V* table... 7
- Changed typical mid bias $I_{S–}$ quiescent current value from 15.2 mA to 16.7 mA in *Electrical Characteristics: V_S = ±12 V* table 7
- Deleted minimum and maximum low bias $I_{S–}$ quiescent current values from *Electrical Characteristics: V_S = ±12 V* table ... 7
- Changed typical low bias $I_{S–}$ quiescent current value from 10.2 mA to 11.2 mA in *Electrical Characteristics: V_S = ±12 V* table..... 7
- Deleted I_{S+} quiescent current "T_A = –40°C to +85°C" test conditions and values from *Electrical Characteristics: V_S =*

The datasheet number will be changing.

Device Family	Change From:	Change To:
THS6212	SBOS758A	SBOS758B

These changes may be reviewed at the datasheet links provided.

http://www.ti.com/product/THS6212

Reason for Change:

To accurately reflect device characteristics.

Anticipated impact on Fit, Form, Function, Quality or Reliability (positive / negative):

No anticipated impact. This is a specification change announcement only. There are no changes to the actual device.

Changes to product identification resulting from this PCN:

None.

Product Affected:

THS6212IRHFR	THS6212IRHFT		

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com